

FIG.1
RELATED ART

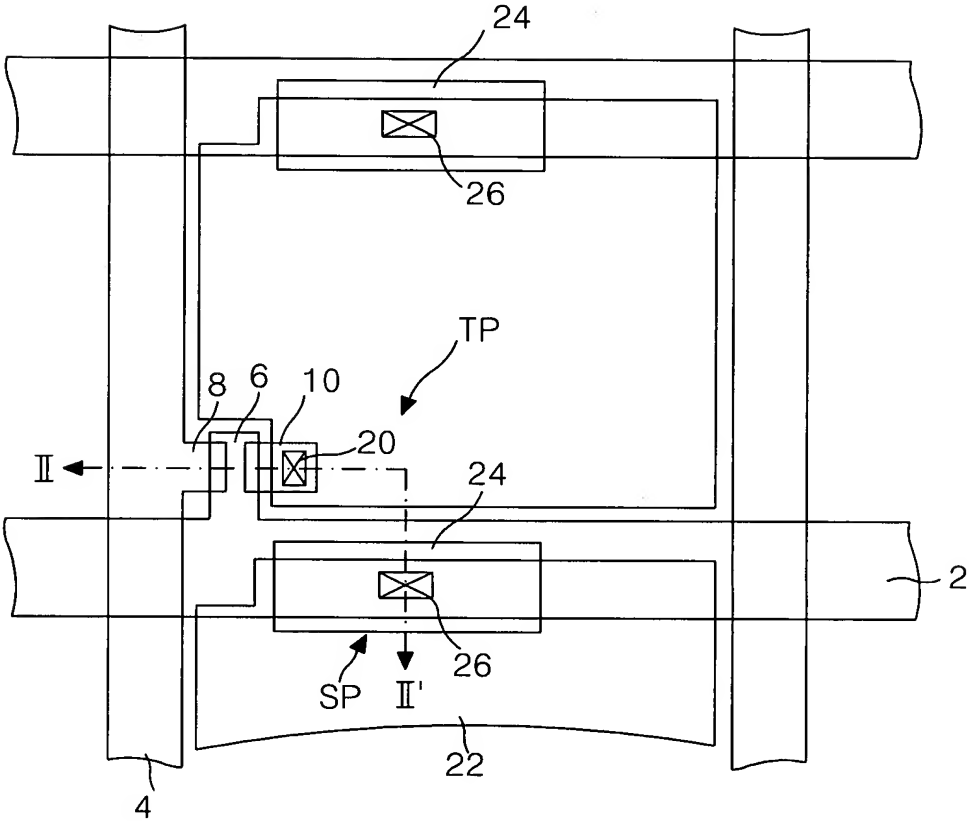


FIG. 2
RELATED ART

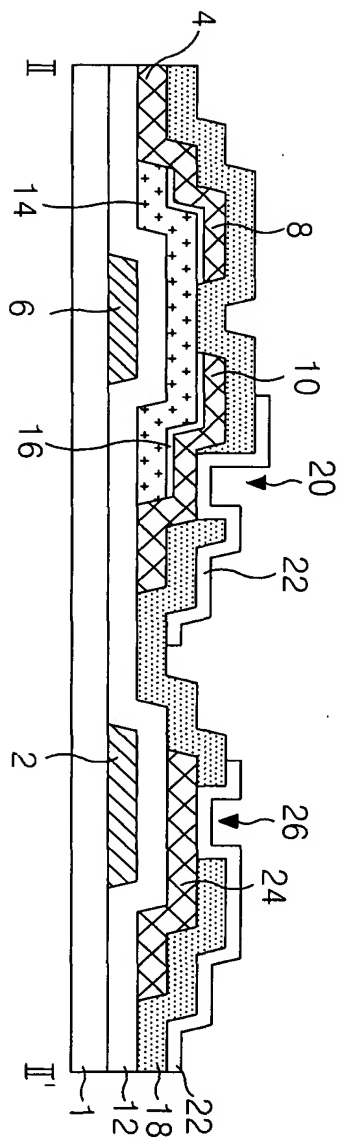


FIG. 3A
RELATED ART

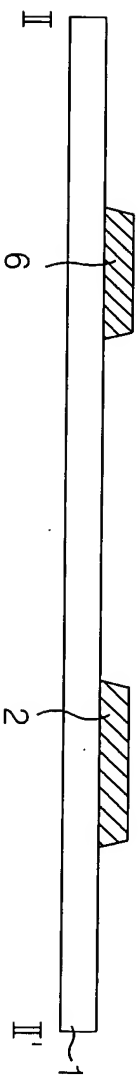
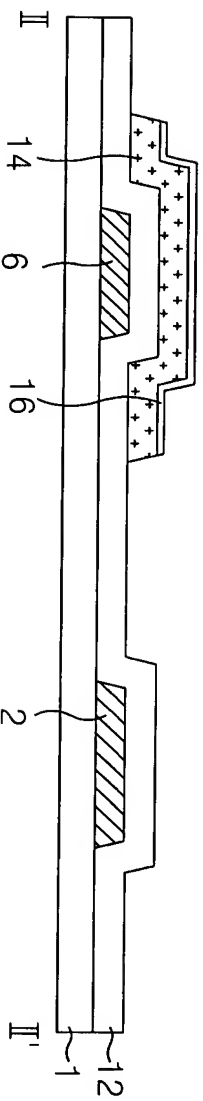
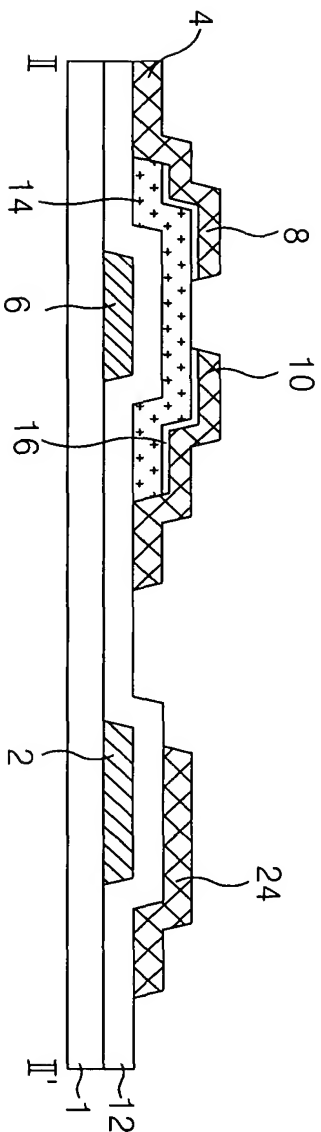


FIG. 3B
RELATED ART





This cross-sectional view shows a semiconductor device with a substrate 1. A first layer 2 is formed on the substrate. A second layer 4 is formed on the first layer. A third layer 6 is formed on the second layer. A fourth layer 8 is formed on the third layer. A fifth layer 10 is formed on the fourth layer. A sixth layer 12 is formed on the fifth layer. A seventh layer 14 is formed on the sixth layer. An eighth layer 16 is formed on the seventh layer. A ninth layer 18 is formed on the eighth layer. A tenth layer 20 is formed on the ninth layer. An eleventh layer 22 is formed on the tenth layer. A twelfth layer 24 is formed on the eleventh layer. A thirteenth layer 26 is formed on the twelfth layer. The device is divided into two regions, II and II', by a vertical line.

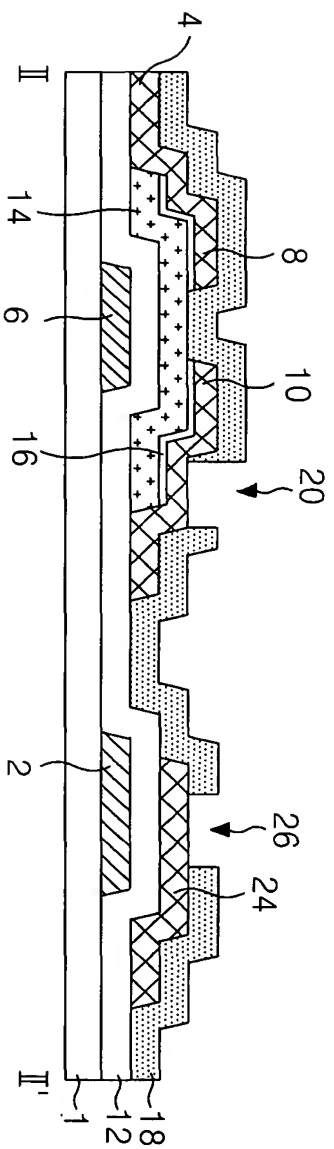


FIG. 3E
RELATED ART

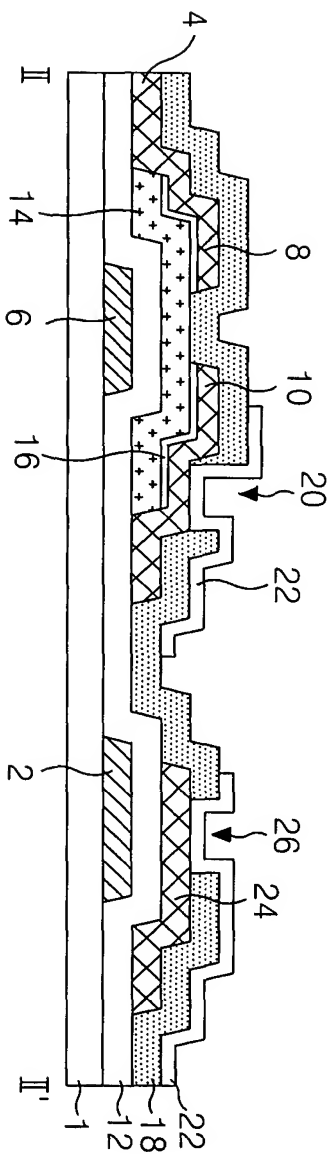


FIG. 4A
RELATED ART

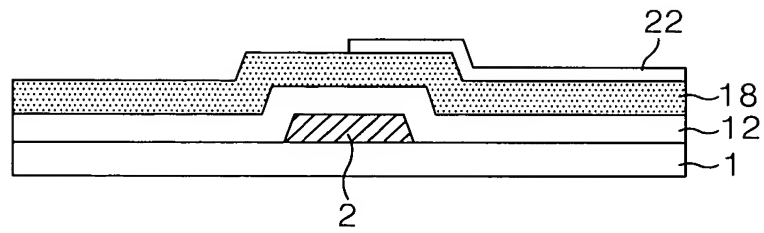


FIG. 4B
RELATED ART

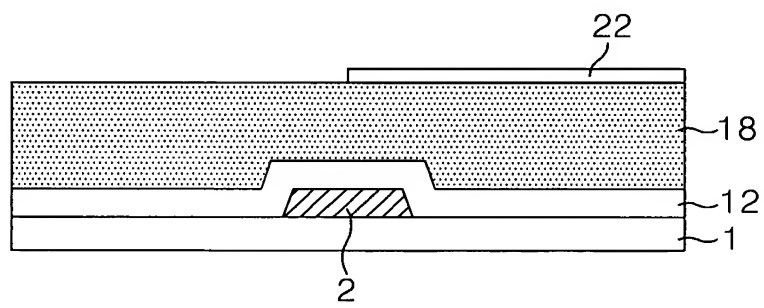


FIG. 5

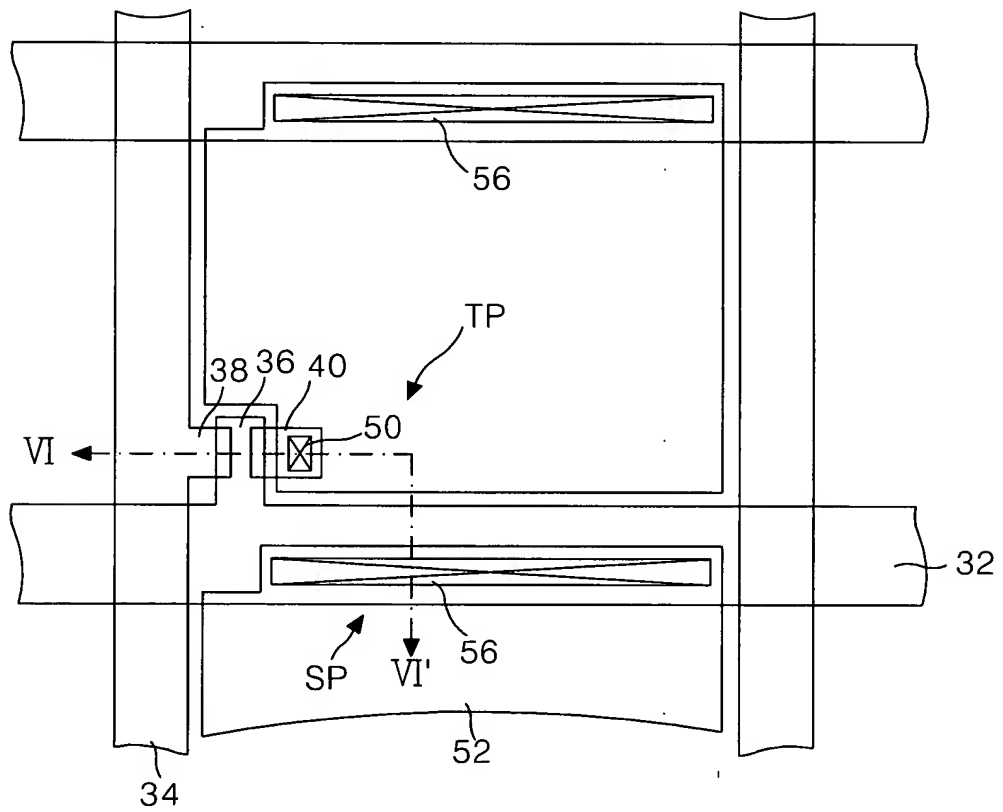


FIG. 6

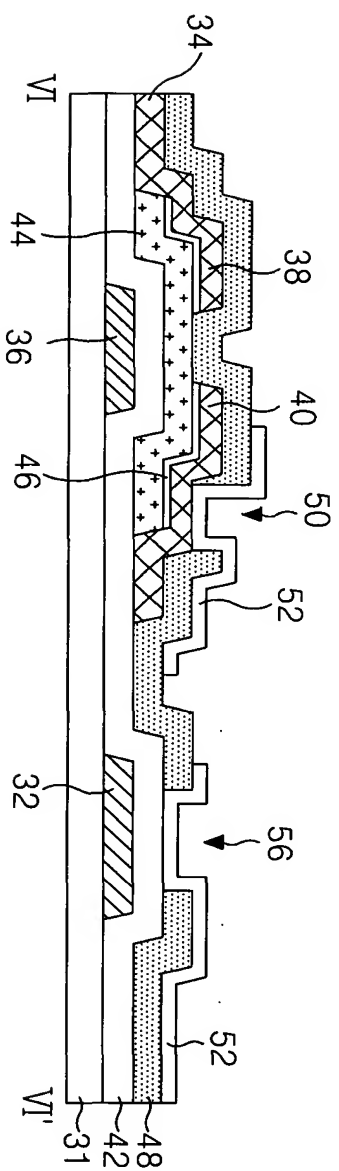


FIG. 7A

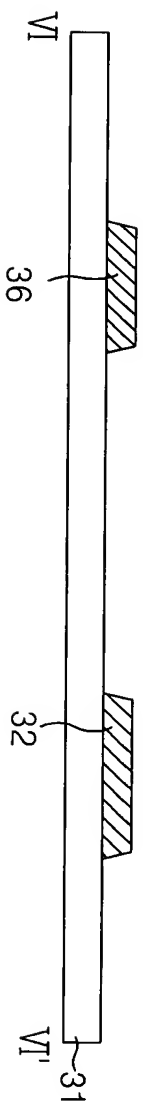


FIG. 7B

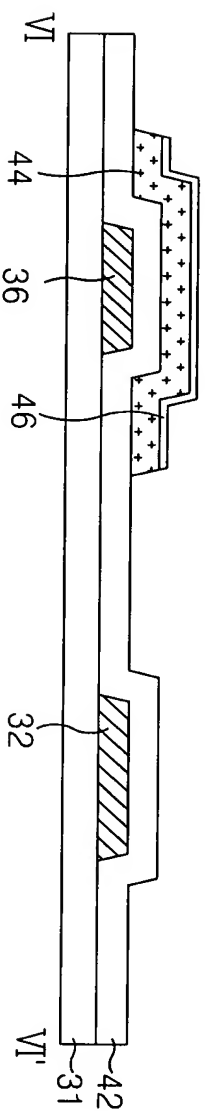


FIG. 7C

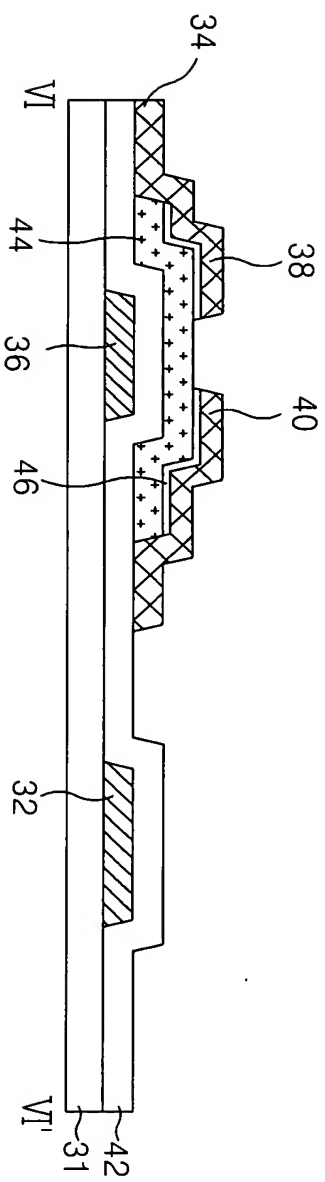


FIG. 7D

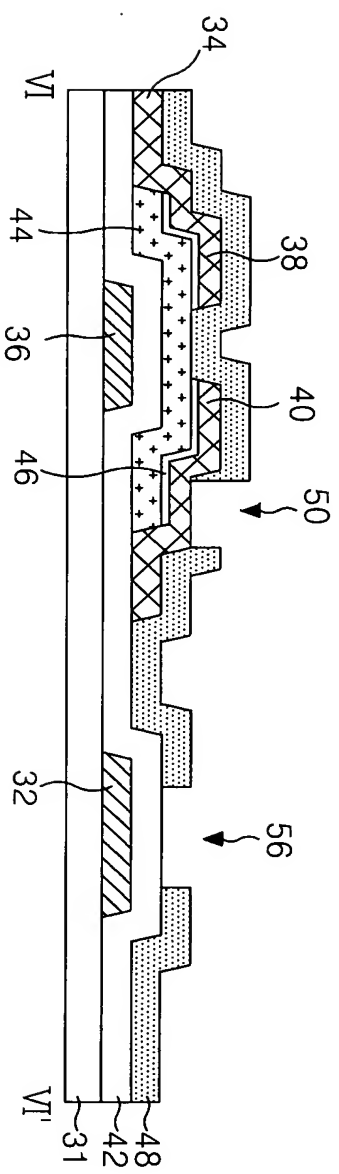


FIG. 7E

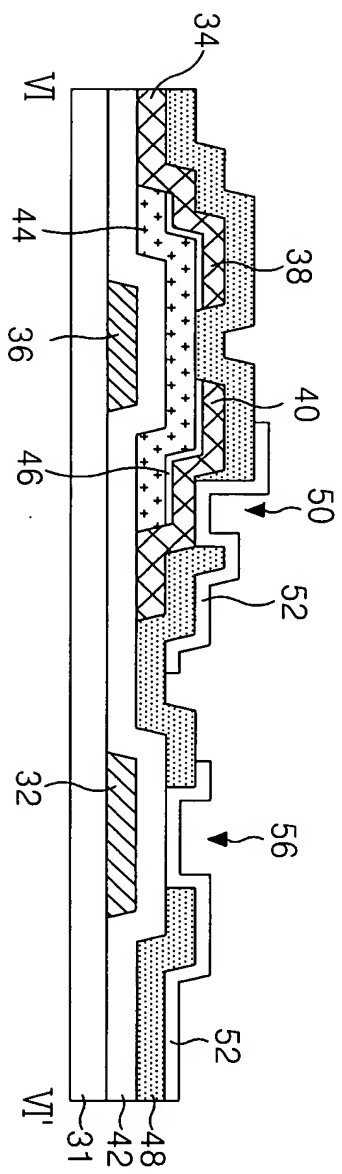


FIG. 8A

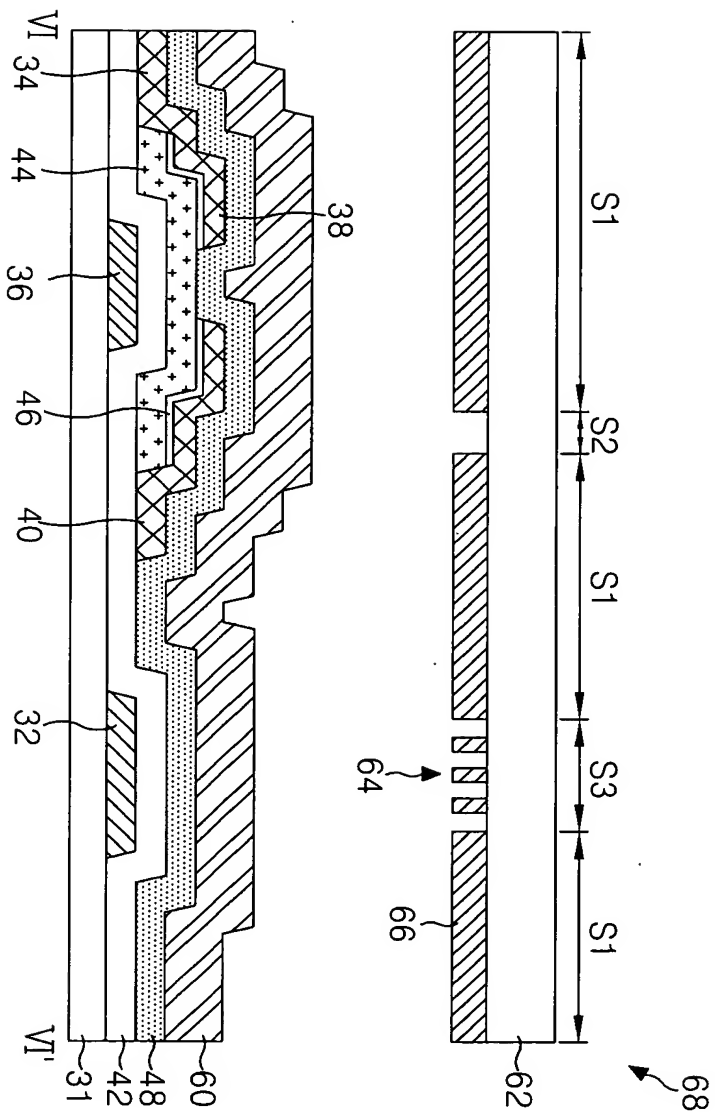


FIG. 8B

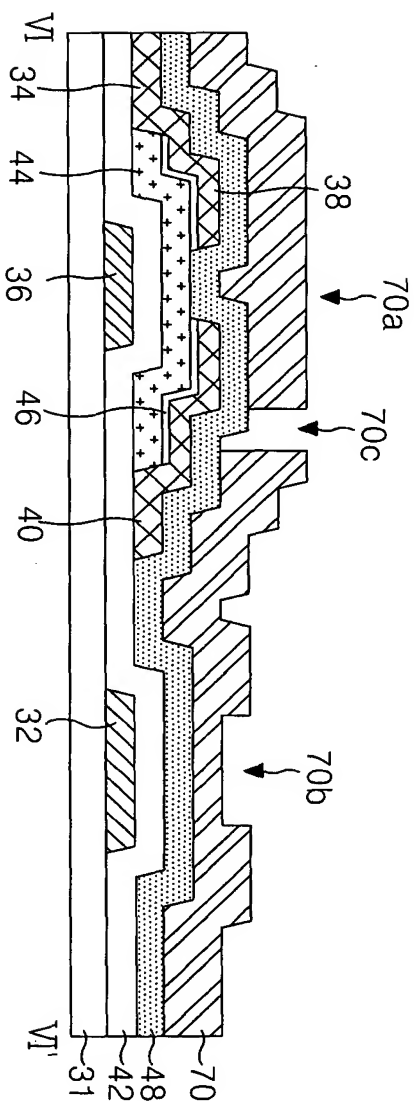


FIG. 8C

